

### IN THE SPECIFICATION

Please amend the specification as follows:

Page 10, line 10, please delete "etch" and insert --etched--.

Page 11, line 17, please insert --(see Figure 3)-- after "108a".

Page 12, line 13, please insert --(see Figure 4)-- after "108b".

Page 12, line 16, please insert -- as shown in Figure 4,-- after "104".

Page 13, line 3, please delete "exposed" and insert --expose--.

Page 13, line 11, please insert --as shown in Figure 5-- after "photoresist".

Page 13, line 11, please delete "As shown in Figure 10," and insert --Figure 10A illustrates subsequent fabrication in which--.

Page 15, line 12, please delete "etch" and insert --etched--.

### IN THE CLAIMS

All claims pending after this amendment are listed below. Please amend the claims as follows:

1. (Amended) A method for making a dielectric structure for dual-damascene applications, the method comprising:
- providing a substrate;
  - fabricating metallization lines within the substrate;
  - forming a barrier layer over the metallization lines and the substrate;
  - forming an inorganic dielectric layer to define a via dielectric layer over the barrier layer, the inorganic dielectric layer being highly selective relative to the barrier layer when etched; and
  - forming a low dielectric constant layer to define a trench dielectric layer over the inorganic dielectric layer.

don't search "inorganic" inherent